

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A method for fabricating a transistor comprising:
forming a gate electrode on a semiconductor substrate;
forming a first preliminary source/drain region and a pocket junction region through a first ion implantation process using the gate electrode as a mask, the pocket junction region being formed under the first preliminary source/drain region;
forming a first oxide layer on the substrate including the gate electrode;
forming a nitride layer on the first oxide layer;
forming a second oxide layer over the nitride layer;
forming spacers on sidewalls of the gate electrode;
forming a second preliminary source/drain region through a second ion implantation process using the spacers as a mask;
removing the nitride layer and the first oxide layer on the surface of the substrate after forming the second preliminary source/drain region through the second ion implantation process using the spacers as a mask; and
diffusing substantially all of the implanted ions in a horizontal direction of the substrate by performing a thermal treatment process for the resulting substrate.

2. (Original) The method as defined by claim 1, further comprising performing a thermal treatment process prior to the removal of the nitride layer and the first oxide layer.